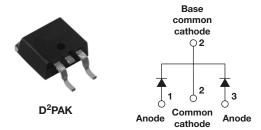


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HALOGEN

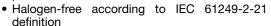
FREE

HEXFRED® Ultrafast Soft Recovery Diode, 2 x 15 A





- Ultrafast recovery
- Ultrasoft recovery
- Very low I_{RRM}
- Very low Q_{rr}
- · Specified at operating conditions
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C



- Compliant to RoHS directive 2002/95/EC
- AEC-Q101 qualified

BENEFITS

- · Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- · Reduced parts count

PRODUCT SUMMARY 600 V V_F at 15 A at 25 °C 1.7 V 2 x 15 A I_{F(AV)} t_{rr} (typical) 19 ns T_{.1} (maximum) 150 °C 80 nC Q_{rr} (typical) dI_{(rec)M}/dt (typical) at 125 °C 160 A/µs 4.0 A I_{RRM} (typical)

DESCRIPTION

VS-HFA30TA60CS is a state of the art center tap ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 15 A per leg continuous current, the VS-HFA30TA60CS is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA30TA60CS is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Cathode to anode voltage	V_{R}		600	V	
Maximum continuous forward current per leg	l _F	T _C = 100 °C	15		
per device			30	Α	
Single pulse forward current	I_{FSM}		150	A	
Maximum repetitive forward current	I _{FRM}		60		
Maximum power dissipation	P _D	T _C = 25 °C	74	°C	
Maximum power dissipation		T _C = 100 °C	29	O	
Operating junction and storage temperature range	T _J , T _{Stg}		- 55 to + 150	W	

Document Number: 94071 Revision: 22-Feb-10

VS-HFA30TA60CSPbF

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ELECTRICAL SPECIFICATIONS PER LEG (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V _{BR}	Ι _R = 100 μΑ		600	-	-	
Maximum forward voltage	V _{FM}	I _F = 15 A	See fig. 1	-	1.3	1.7	V
		I _F = 30 A		-	1.5	2.0	
		I _F = 15 A, T _J = 125 °C		-	1.2	1.6	
Maximum reverse leakage current	I _{RM}	V _R = V _R rated	See fig. 2	-	1.0	10	μΑ
		$T_J = 125$ °C, $V_R = 0.8 \times V_R$ rated		-	400	1000	
Junction capacitance	C _T	V _R = 200 V	See fig. 3	-	25	50	pF
Series inductance	L _S	Measured lead to lead 5 mm from package body		-	8.0	-	nΗ

DYNAMIC RECOVERY CHARACTERISTICS PER LEG (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Reverse recovery time See fig. 5, 10	t _{rr}	$I_F = 1.0 \text{ A}, dI_F/dt = 200 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	19	-	
	t _{rr1}	T _J = 25 °C	I _F = 15 A	-	42	60	ns
	t _{rr2}	T _J = 125 °C		-	70	90	
Peak recovery current See fig. 6	I _{RRM1}	T _J = 25 °C		-	4.0	6.0	A
	I _{RRM2}	T _J = 125 °C		-	6.5	10	
Reverse recovery charge Q_{rr1} $T_J = 25 ^{\circ}C$ See fig. 7 Q_{rr2} $T_J = 125 ^{\circ}C$	$dI_F/dt = 200 A/\mu s$	-	80	180	" C		
	Q _{rr2}	T _J = 125 °C	V _R = 200 V	-	220	450	nC
Peak rate of fall of recovery current during t _b See fig. 8	dI _{(rec)M} /dt1	T _J = 25 °C		-	188	-	- A/µs
	dI _{(rec)M} /dt2	T _J = 125 °C		-	160	-	AνμS

THERMAL - MECHANICAL SPECIFICATIONS PER LEG						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C
Junction to case, single leg conducting	Б		-	-	1.7	
Junction to case, both legs conducting	—— R _{thJC}		-	-	0.85	K/W
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80	
Weight			-	2.0	-	g
			-	0.07	-	oz.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking device		Case style D ² PAK		HFA30TA60CS		

Document Number: 94071 Revision: 22-Feb-10





HEXFRED® Ultrafast Soft Recovery Diode, 2 x 15 A

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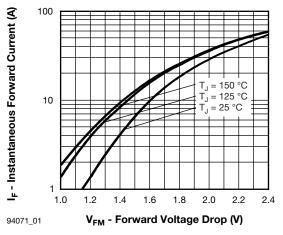


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current (Per Leg)

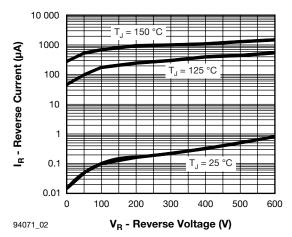


Fig. 2 - Typical Reverse Current vs. Reverse Voltage (Per Leg)

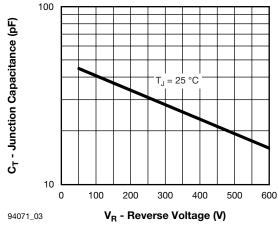


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage (Per Leg)

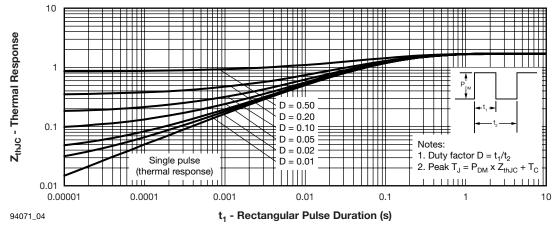


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics (Per Leg)

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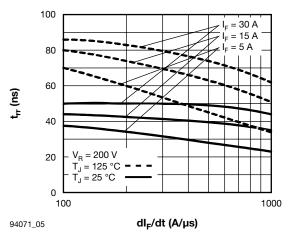


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt (Per Leg)

25

20

15

10

5

0

94071_06

100

.⊤

 $V_{R} = 200 \text{ V}$

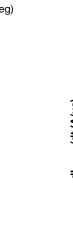
= 125 °C

= 25 °C

= 30 A

 $I_{\rm F} = 15 \, {\rm A}$

 $I_F = 5 A$



1000

6 **dl_F/dt (A/μs)** Fig. 6 - Typical Recovery Current vs. dl_F/dt (Per Leg)

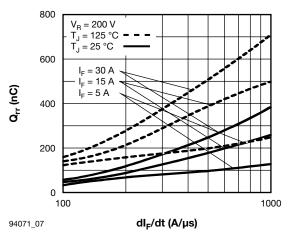


Fig. 7 - Typical Stored Charge vs. dI_F/dt (Per Leg)

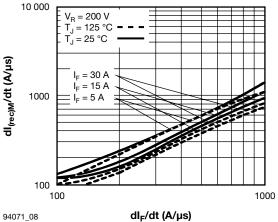


Fig. 8 - Typical $dI_{(rec)M}/dt$ vs. dI_F/dt (Per Leg)

Document Number: 94071 Revision: 22-Feb-10



HEXFRED® Ultrafast Soft Recovery Diode, 2 x 15 A

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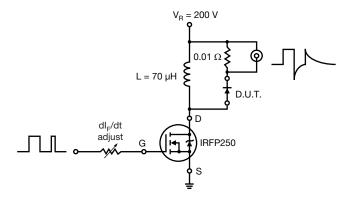
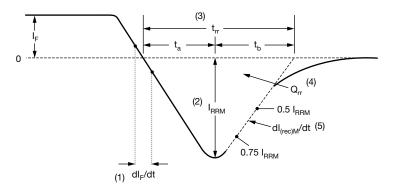


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (4) $\rm Q_{rr}$ area under curve defined by $\rm t_{rr}$ and $\rm I_{RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) dl_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

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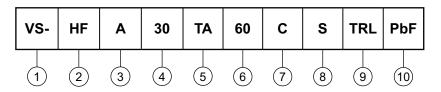
HEXFRED®





ORDERING INFORMATION TABLE

Device code



1 - HPP product suffix

2 - HEXFRED® family

3 - Process designator: A = Electron irradiated

- Current rating (30 = 30 A)

5 - Package outline (TA = TO-220, 3 leads)

6 - Voltage rating (60 = 600 V)

7 - Circuit configuration (C = Common cathode)

9 - • None = Tube (50 pieces)

• TRL = Tape and reel (left oriented)

• TRR = Tape and reel (right oriented)

- PbF = Lead (Pb)-free

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95046				
Part marking information	www.vishay.com/doc?95054				
Packaging information	www.vishay.com/doc?95032				

Document Number: 94071 Revision: 22-Feb-10

6



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